

EXHIBIT 21

July 25, 2005

Claim 85 (New): A method of depositing a film on a substrate, comprising:
providing a process gas between a target and a substrate;
providing pulsed DC power to the target;
providing a magnetic field to the target; and
wherein a material is deposited on the substrate, and an oxide film is formed by reactive sputtering in transition mode.

December 21, 2005

Claim 85 (Currently amended): A method of depositing a film on a substrate, comprising:
providing a process gas between a target and a substrate;
providing pulsed DC power to the target;
providing a magnetic field to the target; and
wherein a material is deposited on the substrate, and an oxide film is formed by reactive sputtering in ~~transition mode~~ a mode between a metallic mode and a poison mode.

December 18, 2007

Claim 85 (Currently amended): A method of depositing ~~[[a]]~~ an insulating film on a substrate, comprising:
providing a process gas between a target and a substrate;
providing pulsed DC power to the target through a narrow band rejection filter such that the voltage on the target alternates between positive and negative voltages;
providing an RF bias that corresponds to the narrow band rejection filter to the substrate;
and
providing a magnetic field to the target; ~~and~~
wherein ~~[[a]]~~ an oxide material is deposited on the substrate, and ~~an oxide~~ the insulating film is formed by reactive sputtering in a mode between a metallic mode and a poison mode.

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